

# MA3G751, MA3G751A

Silicon epitaxial planar type (cathode common)

For switching power supply

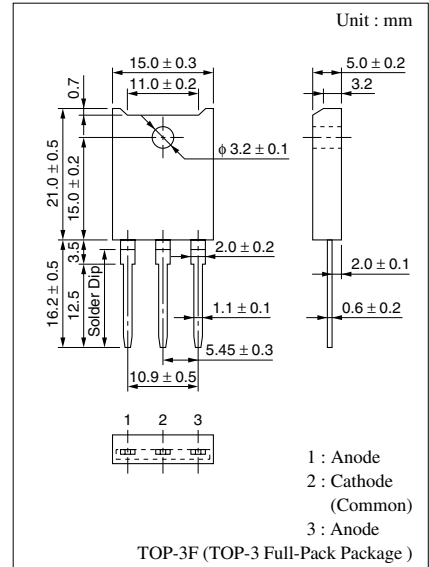
## ■ Features

- Forward current (average)  $I_{F(AV)}$ : 20 A type
- High reliability caused by sealed in the TOP-3F (Full-pack package)
- Cathode common dual type
- Low forward rise voltage  $V_F$

## ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Repetitive peak reverse voltage	MA3G751	$V_{RRM}$	40	V
	MA3G751A		45	
Average forward current		$I_{F(AV)}$	20	A
Non-repetitive peak forward surge current*		$I_{FSM}$	150	A
Junction temperature		$T_j$	-40 to +125	$^\circ\text{C}$
Storage temperature		$T_{stg}$	-40 to +125	$^\circ\text{C}$

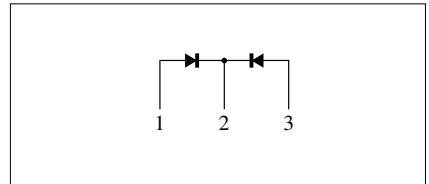
Note) \* : Half sine-wave: 10 ms/cycle



## Marking Symbol

- MA3G751 : MA3G751
- MA3G751A : MA3G751A

## Internal Connection



## ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	MA3G751	$V_R = 40\text{ V}$			5	mA
	MA3G751A	$V_R = 45\text{ V}$			5	
Forward voltage (DC)	$V_F$	$I_F = 10\text{ A}$			0.55	V
Thermal resistance	$R_{th(j-c)}$	Direct current (between junction and case)			1.5	$^\circ\text{C/W}$

Note) Rated input/output frequency: 100 MHz

